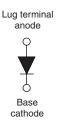
Vishay Semiconductors

## High Performance Schottky Rectifier, 120 A



www.vishay.com

HALF-PAK (D-67)



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub> 120 A				
V <sub>R</sub>	45 V			
Package	HALF-PAK (D-67)			
Circuit configuration Single diode				

### **FEATURES**

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- · Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### DESCRIPTION

The VS-121NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS VALUES UNITS					
I <sub>F(AV)</sub>	Rectangular waveform	120	A			
V <sub>RRM</sub>		45	V			
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	16 000	A			
V <sub>F</sub>	120 A <sub>pk</sub> , T <sub>J</sub> = 125 °C	0.6	V			
TJ	Range	-55 to +175	°C			

VOLTAGE RATINGS						
PARAMETER	SYMBOL	VS-121NQ045PbF	UNITS			
Maximum DC reverse voltage	V <sub>R</sub>	45	V			
Maximum working peak reverse voltage	V <sub>RWM</sub>	40	v			

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDI	VALUES	UNITS		
Maximum average forward current See fig. 5	I <sub>F(AV)</sub>	50 % duty cycle at $T_C$ = 137 °C,	120	A		
Maximum peak one cycle non-repetitive surge current	I	5 µs sine or 3 µs rect. pulse Following any rated load condition and with rated		16 000	А	
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse			~	
Non-repetitive avalanche energy	E <sub>AS</sub>	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 13 A, L = 1 mH		81	mJ	
Repetitive avalanche current	I <sub>AR</sub>	Current decaying linearly to zero in 1 $\mu$ s Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical		13	А	

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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS		
		120 A	T <sub>.1</sub> = 25 °C	0.65		
Maximum forward voltage drop	V <sub>FM</sub> <sup>(1)</sup>	240 A	1j=25 C	0.82	V	
See fig. 1	VFM (')	120 A	T.I = 125 °C	0.6		
		240 A	1j = 125 C	0.76		
Maximum reverse leakage current		$T_J = 25 \ ^{\circ}C$	$V_{\rm B}$ = Rated $V_{\rm B}$	10		
See fig. 2	I <sub>RM</sub>	T <sub>J</sub> = 125 °C	$v_{\rm R} = naleu v_{\rm R}$	90	mA	
Maximum junction capacitance	CT	V <sub>R</sub> = 5 V <sub>DC</sub> (test signal ran	5200	pF		
Typical series inductance	L <sub>S</sub>	From top of terminal hole	7.0	nH		
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>	10 000	V/µs		

#### Note

<sup>(1)</sup> Pulse width = 500  $\mu$ s

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Maximum junction and storage te	mperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to 175	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.38	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.05		
Approvimete weight				30	g	
Approximate weight	Approximate weight			1.06	oz.	
Mounting torque minimum maximum				3 (26.5)	N ⋅ m (lbf ⋅ in)	
			Non-lubricated threads	4 (35.4)		
Terminal torque minimum maximum			Non-Iudricated trireads	3.4 (30)		
				5 (44.2)		
Case style				HALF-PA	K module	

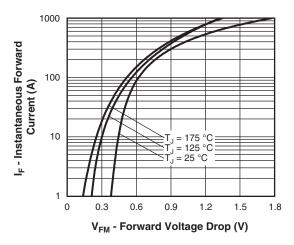
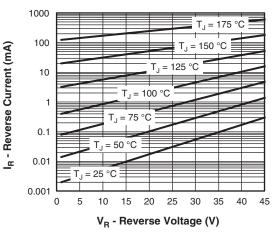
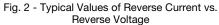


Fig. 1 - Maximum Forward Voltage Drop Characteristics





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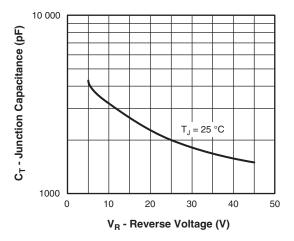


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

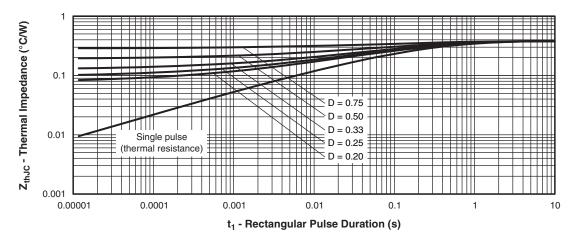
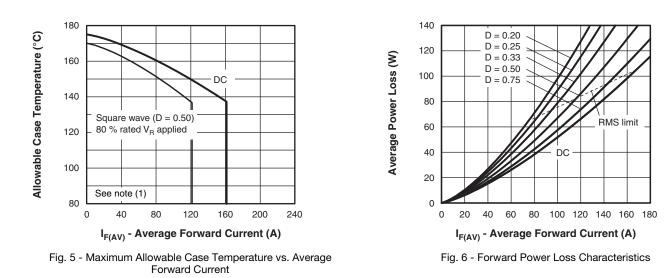


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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## VS-121NQ045PbF

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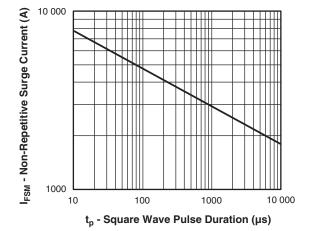
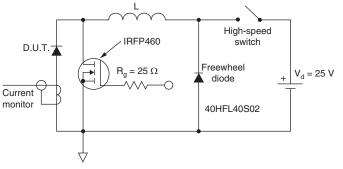


Fig. 7 - Maximum Non-Repetitive Surge Current



#### Fig. 8 - Unclamped Inductive Test Circuit

#### Note

- $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \mbox{forward power loss} = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = \ \mbox{inverse power loss} = V_{R1} \ x \ I_R \ (1 D); \ I_R \ at \ V_{R1} = \ rated \ V_R \end{array}$

### **ORDERING INFORMATION TABLE**

Device code	VS-	12	1	Ν	Q	045	PbF
	1	2	3	4	5	6	7
	1 -	Visl	nay Sem	niconduc	ctors pro	oduct	
	2 - Average current rating (x 10)						
	3 - Product silicon identification						
	4 - N = not isolated						
	5 - Q = Schottky rectifier diode						
	6 - Voltage rating (045 = 45 V)						
	7 -	Lea	d (Pb)-f	ree			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95020				
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17.5 (0.69) 16.5 (0.65)



### **DIMENSIONS** in millimeters (inches)

SHAY





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